



Average gate power dissipation ( $T_j=150$ )	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	4	kV

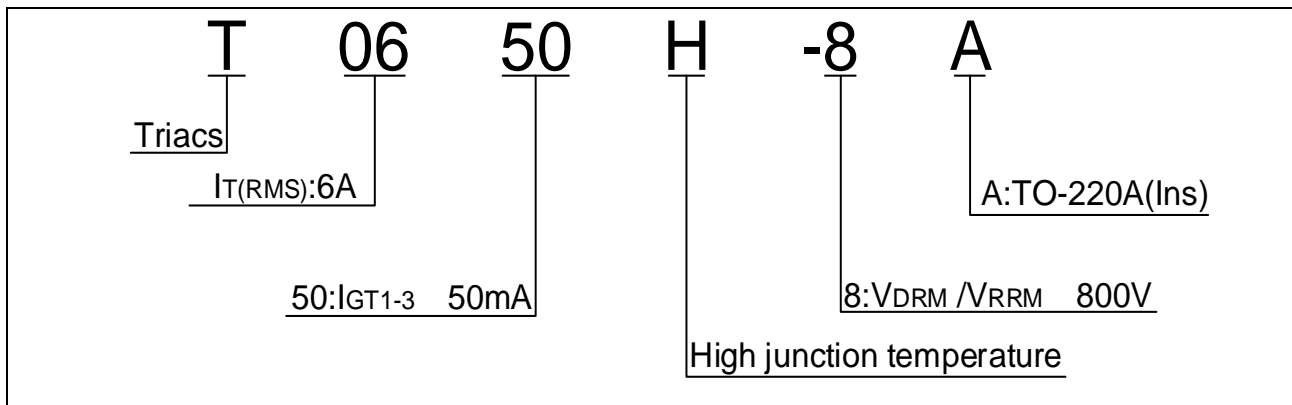
ELECTRICAL CHARACTERISTICS ( $T_j=25$  unless otherwise specified)

Symbol	Test Condition	Ques	Value	Unit	
$I_{GT}$	$V_D=12V R_L=33$	-	MAX.	50	mA
$V_{GT}$		-	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM} T_j=150$ $R_L=3.3k$	-	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	-	MAX.	70	mA
				100	
$I_H$	$I_T=100mA$		MAX.	50	mA
$dV/dt$	$V_D=540V$ Gate Open $T_j=150$		MIN.	1200	V/s
$(dI/dt)_c$	$V_j=150$		MIN.	5	A/ms
$t_{on}$	$I_G=80mA I_A=400mA I_R=40mA$ $T_j=25$		TYP.	5	s
$t_{off}$				50	

STATIC CHARACTERISTICS

Symbol	Parameter	Value (MAX.)	Unit	
$V_{TM}$	$I_{TM}=8.5A t_p=380$ s $T_j=25$	1.4	V	
$V_{TO}$	Threshold voltage $T_j=150$	0.8	V	
$R_D$	Dynamic resistance $T_j=150$	63	$\Omega$	
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	A
$I_{RRM}$		$T_j=150$	1	mA

ORDERING INFORMATION



MARKING

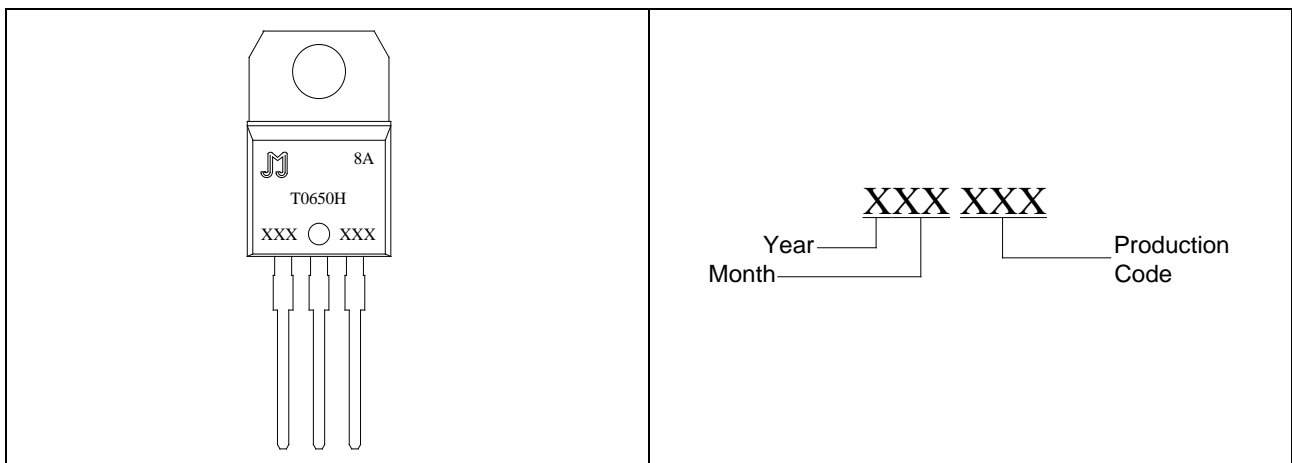


FIG.1: Maximum power dissipation versus RMS on-state current

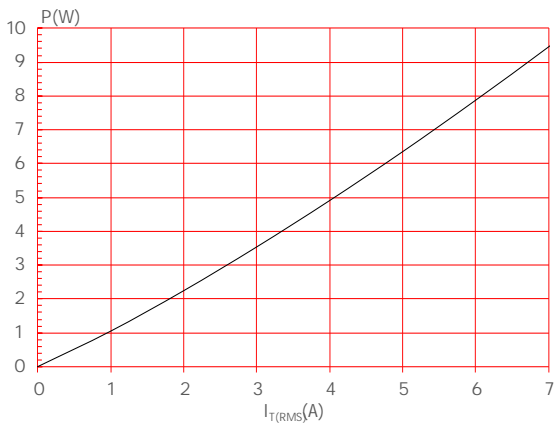
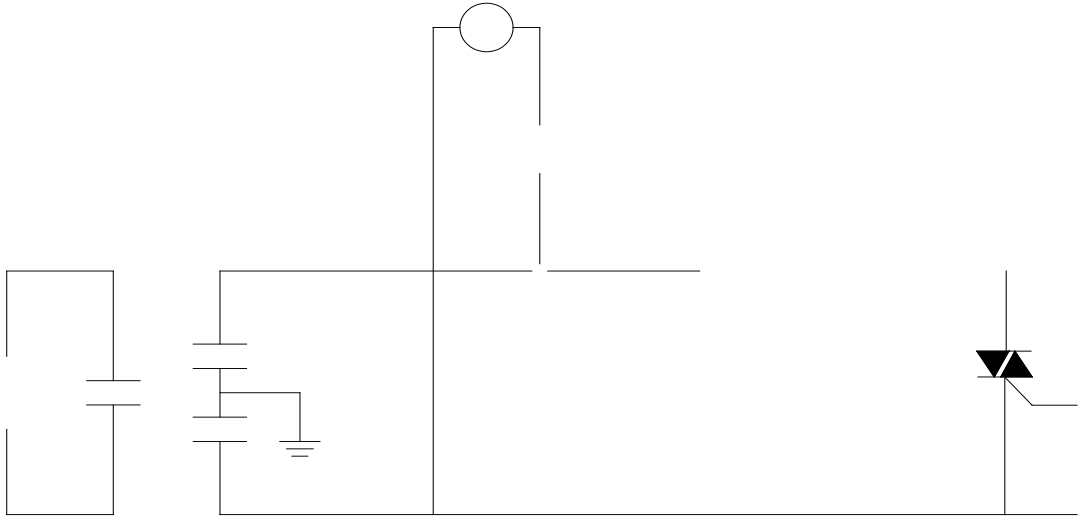


FIG.2: RMS on-state current versus case temperature



FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards




ORDERING INFORMATION

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(A <sub>m</sub> ) H	Package	Base pin (pins)	Delivery date
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